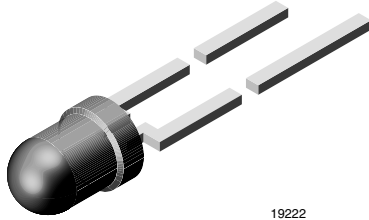


High Intensity LED in \varnothing 3 mm Tinted Diffused Package



19222

DESCRIPTION

This device has been designed to meet the increasing demand for AllnGaP technology.

It is housed in a 3 mm clear plastic package. The wide viewing angle of these devices provides a high on-off contrast.

All packing units are categorized in luminous intensity groups. That allows users to assemble LEDs with uniform appearance.

PRODUCT GROUP AND PACKAGE DATA

- Product group: LED
- Package: 3 mm
- Product series: standard
- Angle of half intensity: $\pm 60^\circ$

FEATURES

- AllnGaP technology
- Standard \varnothing 3 mm (T-1) package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very wide viewing angle
- Luminous intensity categorized
- Lead (Pb)-free device

APPLICATIONS

- Status lights
- OFF/ON indicator
- Background illumination
- Readout lights
- Maintenance lights
- Legend light

PARTS TABLE

PART	COLOR, LUMINOUS INTENSITY	TECHNOLOGY
TLHK4600	Red, $I_V > 6.3$ mcd	AllnGaP on GaAs

ABSOLUTE MAXIMUM RATINGS¹⁾ TLHK4600

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
DC Forward current	$T_{amb} \leq 60^\circ\text{C}$	I_F	30	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	0.1	A
Power dissipation	$T_{amb} \leq 60^\circ\text{C}$	P_V	80	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 55 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from body	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient		R_{thJA}	400	K/W

Note:

¹⁾ $T_{amb} = 25^\circ\text{C}$, unless otherwise specified

OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ TLHK4600, RED						
PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP.	MAX	UNIT
Luminous intensity ²⁾	$I_F = 10 \text{ mA}$	I_V	6.3	15		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$	λ_d		630		nm
Peak wavelength	$I_F = 10 \text{ mA}$	λ_p		643		nm
Angle of half intensity	$I_F = 10 \text{ mA}$	φ		± 60		deg
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.9	2.6	V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		15		pF
Reverse voltage	$I_R = 10 \text{ }\mu\text{A}$	V_R	5			V

Note:

1) $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

2) in one packing unit $I_{Vmin}/I_{Vmax} \leq 0.5$

TYPICAL CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

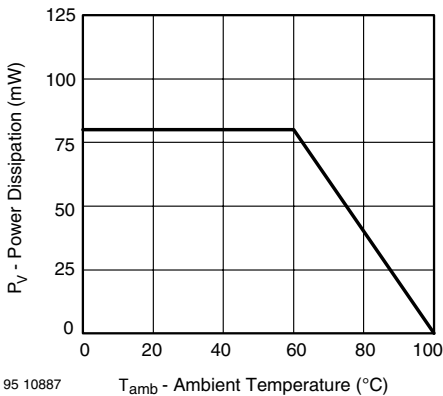


Figure 1. Power Dissipation vs. Ambient Temperature

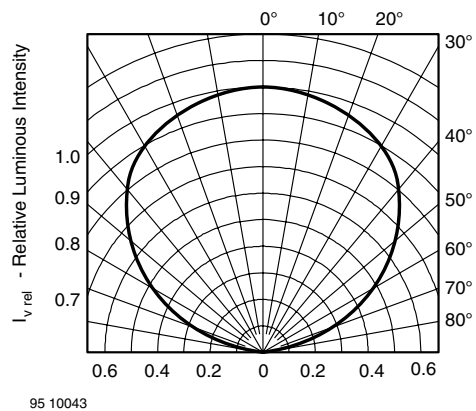


Figure 3. Rel. Luminous Intensity vs. Angular Displacement

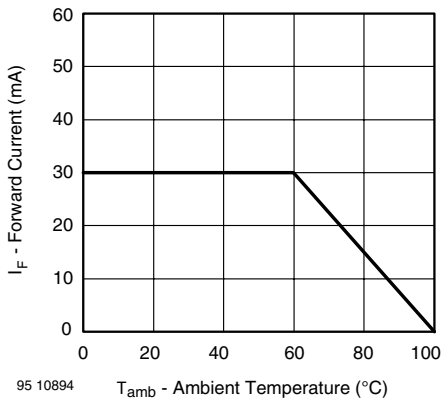


Figure 2. Forward Current vs. Ambient Temperature for InGaN

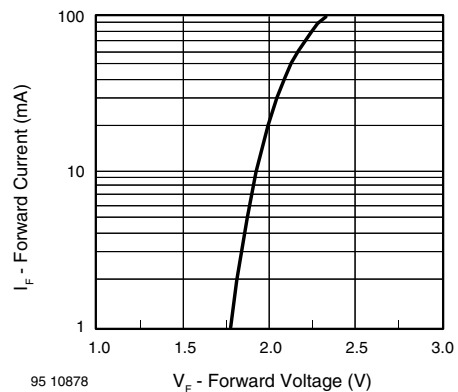
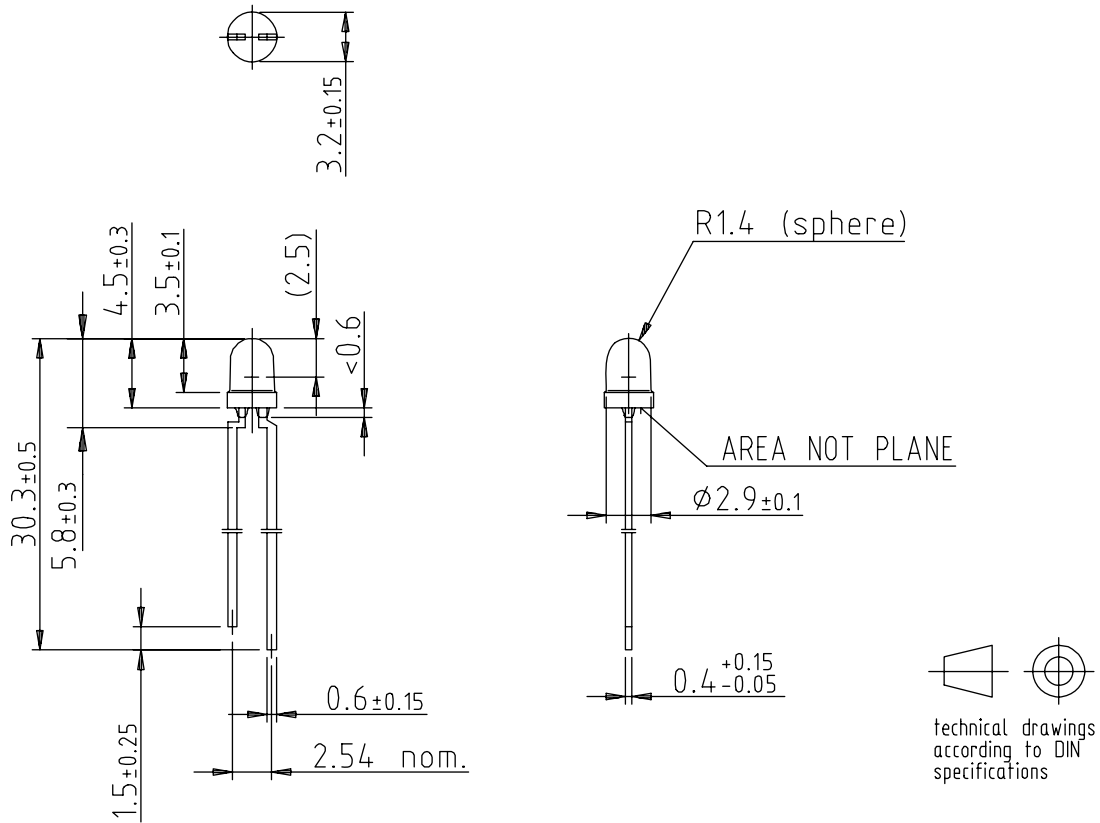


Figure 4. Forward Current vs. Forward Voltage

PACKAGE DIMENSIONS in millimeters



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